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"1 &amp;KDQQHO 3RZHU 026)(7

"5

"\$YDODQFKH (QHUJ\ 6SHFLILHG

"6

",s\ 0DQG 9RQ 6SHFLILHG DW (OHYD u€p0 XPSHUDPu€P€

3DUDPHWHU	6\PERO	9DOXH	8QLW
Drain-Source Voltage	VDS	600	V
Gate-Source Voltage	VGS	±30	
Continuous Drain Current	ID	1	A
Pulsed Drain Current	IDM	9	
Power Dissipation	PD		W
Single Pulsed Avalanche Energy*	EAS	20	mJ
Thermal Resistance IURP Junction to Ambient	RhJA		/W
Junction Temperature	TJ	150	/
Storage Temperature	Tstg	-50 ~+150	

\*EAS condition: Tj=25 / , VDD=100V, VG=10V, L=10mH, I=2A, RG=25 Ÿ

